

HIGH CURRENT APPLICATION.

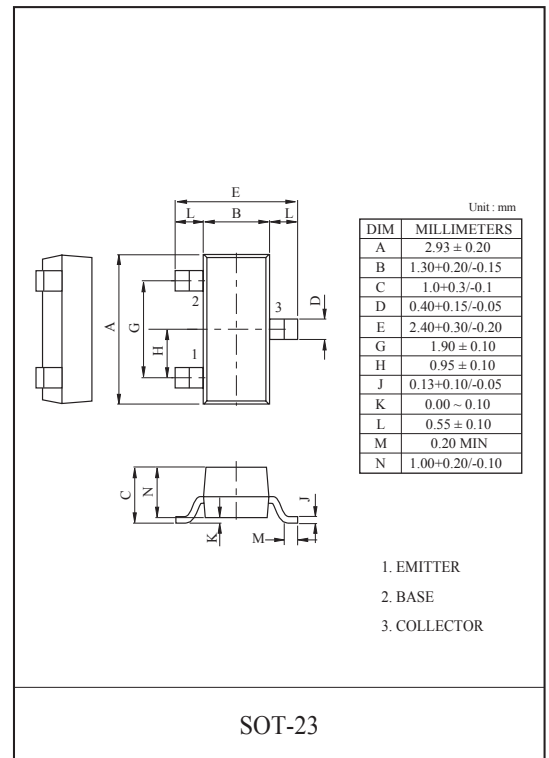
FEATURE

- Complementary to KTC8050S.
- Suffix U : Qualified to AEC-Q101.
ex) KTC8550S-D-RTK/PU

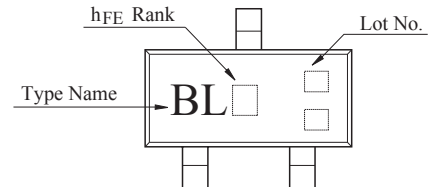
MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-35	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Emitter Current	I_E	800	mA
Collector Power Dissipation	P_C^*	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 ~ 150	°C

* P_C : Package Mounted On 99.5% Alumina (10×8×0.6mm)



Marking



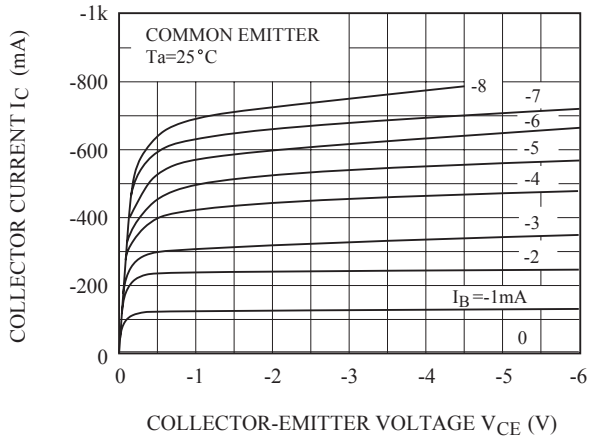
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-15V, I_E=0$	-	-	-50	nA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-0.5mA, I_E=0$	-35	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-30	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=-1V, I_C=-50mA$	100	-	300	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-350mA$	60	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$	-	-	-0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-1V, I_C=-500mA$	-	-	-1.2	V
Transition Frequency	f_T	$V_{CE}=-5V, I_C=-10mA$	-	120	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, f=1MHz, I_E=0$	-	19	-	pF

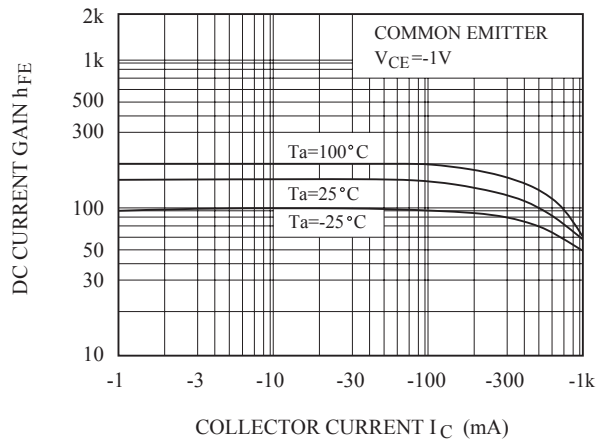
Note : $h_{FE(1)}$ Classification C : 100 ~ 200, D : 150 ~ 300

KTC8550S

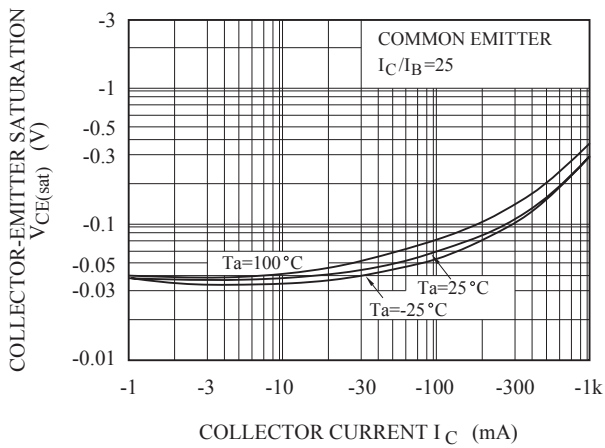
$I_C - V_{CE}$



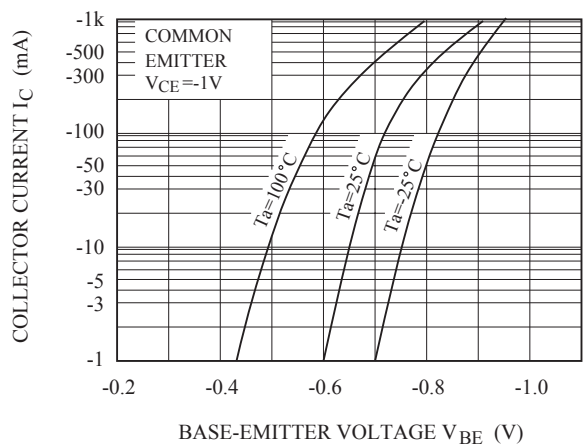
$h_{FE} - I_C$



$V_{CE(sat)} - I_C$



$I_C - V_{BE}$



$P_c - T_a$

